

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2040347	substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 13:32
S2	1361	plating and transferring and heating and annealing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 12:47
S3	1234	S1 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 12:47
S4	2673653	processing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 12:47
S5	1078	S3 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 12:48
S6	276	cleaning and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 13:29
S7	467	438/584.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 13:22
S8	1	S6 and S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 13:22

S9	0	"annealing done at a temperature"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 13:29
S10	55032	annealing near5 temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 13:30
S11	18683	semiconductor and S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 13:30
S12	62	S6 and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:15
S13	16385	copper adj plating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:15
S14	3708	cleaning adj bath	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:15
S15	23736	annealing adj temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:16
S16	0	S13 and S14 and S15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:16

S17	123	S13 and S15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:16
S18	783365	cleaning	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:16
S19	38	S17 and S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:42
S20	3	"6709970".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:43
S21	4128738	S20 and annealing temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:43
S22	1	S20 and annealing adj temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:45
S23	1	"6692588".pn. and annealing adj temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:45
S24	1	"6692588".pn. and annealing adj temperature and plating and cleaning	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 15:14

S25	2	"20040043598"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:47
S26	1	"20040043598" and annealing adj temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 14:48
S27	1	"20020130046" and annealing adj temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 15:05
S28	1	"20020130046" and annealing adj temperature and cleaning	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 08:31
S29	0	"20010024691" and annealing adj temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 15:38
S30	1	"20010024691" and rinsing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 15:16
S31	1	S30 and heating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 15:23
S32	206	substrate adj cleaning near5 drying	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 15:32

S33	166	semiconductor and S32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 15:28
S34	68	S33 and (heat or heating)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 15:28
S35	3	substrate adj cleaning near5 drying adj time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 15:32
S36	1	"20010024691" and annealing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 15:39
S37	1	heating and S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 15:39
S38	183	in-situ adj processing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 08:31
S39	89	S38 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 08:34
S40	0	2002/0130046 and rinsing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 08:34

S41	2	"6692588".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 10:23
S42	1	"20010024691" and heating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 11:35
S43	0	"20010024691" and heating near5 cleaning	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 11:35
S44	0	"20010024691" and heating near10 cleaning	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 11:38
S45	1	substrate adj processing adj appartus	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 11:39
S46	1	subtrate adj processing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 11:41
S47	15700	substrate adj processing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 11:41
S48	10381	semiconductor and S47	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 11:42

S49	151	plating and cleaning and annealing and heating and S48	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:23
S50	16	("20020004301" "20020029961" "4788994" "5192087" "5972192" "6017437" "6080042" "6176992" "6254760" "6258220" "6267853" "6395094" "6508920" "6551488" "6558518" "6612915").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/12 11:45
S51	1	mos adj gate adj oxidation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 12:58
S52	183	in-situ adj processing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:05
S53	297	uzoh.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:15
S54	2673754	S53 and substrate processing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:16
S55	10	S53 and substrate adj processing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:27
S56	22022	substrate adj process\$3 and semiconductors	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:24

S57	513	cleaning and rinsing and plating and annealing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:25
S58	118	S56 and S57	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:25
S59	109	heating and S58	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:25
S60	0	S58 and heated adj rinse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:27
S61	19	S58 and rinsing adj solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:27
S62	2	"6692588"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 14:31
S63	55060	annealing near5 temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 10:47
S64	55060	S63	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 10:48

S65	7179	drying and S64	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 10:49
S66	1323	semiconductor and S65	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 10:52
S67	677	semiconductor and substrate adj cleaning and drying and time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 10:53
S68	42	semiconductor and substrate adj cleaning and drying adj time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 10:58
S69	38	semiconductor and substrate adj cleaning and drying adj time and seconds	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 10:59
S70	23	semiconductor and substrate adj cleaning and drying adj time and minutes	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 11:10
S71	795565	semiconductor and(substrate or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 11:11
S72	795565	semiconductor and (substrate or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 11:10

S73	10188	cleaning and drying and S72	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 11:11
S74	0	S72 and robot adj arm adj trasfer and time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 11:12
S75	6349	S72 and robot and transfer and time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 11:12
S76	5901	S75 and seconds	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 11:22
S77	7842003	"20010024691" and drying time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 11:22
S78	0	"20010024691" and drying adj time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 11:23
S79	3	"20010024691"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 11:23
S80	1	S79 and transfer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 11:23

S81	76	substrate adj processing and drying adj time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:21
S82	49	S81 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 13:43
S83	278	substrate adj process\$4 and transfer adj time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 13:46
S84	262	S83 and seconds	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 13:47
S85	199	S84 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 13:48
S86	5	transfer adj time near7 annealing and cleaning	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 13:49
S87	14568	cleaning and annealing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 13:49
S88	1572112	semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 13:50

S89	2267785	substrate or wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 13:50
S90	7879	S87 and S88 and S89	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 13:50
S91	7842135	S90 and transfer time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 13:51
S92	53	S90 and transfer adj time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:02
S93	169	S90 and temperature adj controller	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:04
S94	28	annealing adj chamber and temperature adj controller	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:05
S95	24	annealing adj chamber and temperature adj controller and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:05
S96	22	annealing adj chamber and temperature adj controller and semiconductor and (substrate or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:09

S97	0	rinsing adj chamber and temperature adj controller and semiconductor and (substrate or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:10
S98	46	substrate adj processing and rinsing and temperature adj controller	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:11
S99	2	substrate adj processing and rinsing and temperature adj controller and thermocouple	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:13
S10 0	71	substrate adj processing and cleaning and temperature adj controller and thermocouple	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:15
S10 1	3	semiconductor and substrate adj processing and cleaning and temperature near7 controlled near7 rinse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:18
S10 2	3309	semiconductor and substrate adj processing and cleaning	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:18
S10 3	4146	substrate adj processing and cleaning	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:37
S10 4	173	S103 and temperature adj controller	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:22

S10 5	834	substrate adj processing and rinsing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:38
S10 6	46	S105 and temperature adj controller	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 14:47
S10 7	2	S105 and temperature adj controller and thermocouple	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 15:05
S10 8	0	"5817185".pn. and thermocouple	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 15:06
S10 9	21	semiconductor and rinsing adj fluid and thermocouple	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/15 15:06
S11 0	10847	controller same thermocouple	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:24
S11 1	156	electroplating and S110	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:24
S11 2	46	(rinse or rinsing) and S111	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:25

S11 4	2	"20040097071"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:25
S11 5	1	"20040097071" and S112	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:44
S11 6	1	S115 and drying	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:44